Surface Mount Schottky Power Rectifier

POWERMITE[®] Power Surface Mount Package

The Schottky Powermite[®] employs the Schottky Barrier principle with a barrier metal and epitaxial construction that produces optimal forward voltage drop–reverse current tradeoff. The advanced packaging techniques provide for a highly efficient micro miniature, space saving surface mount Rectifier. With its unique heatsink design, the Powermite[®] has the same thermal performance as the SMA while being 50% smaller in footprint area, and delivering one of the lowest height profiles, < 1.1 mm in the industry. Because of its small size, it is ideal for use in portable and battery powered products such as cellular and cordless phones, chargers, notebook computers, printers, PDAs and PCMCIA cards. Typical applications are AC–DC and DC–DC converters, reverse battery protection, and "ORing" of multiple supply voltages and any other application where performance and size are critical.

Features

- Low Profile Maximum Height of 1.1 mm
- Small Footprint Footprint Area of 8.45 mm²
- Low V_F Provides Higher Efficiency and Extends Battery Life
- Supplied in 12 mm Tape and Reel
- Low Thermal Resistance with Direct Thermal Path of Die on Exposed Cathode Heat Sink
- Pb–Free Packages are Available

Mechanical Characteristics:

- Powermite[®] is JEDEC Registered as D0–216AA
- Case: Molded Epoxy
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 16.3 mg (Approximately)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Maximum for 10 Seconds



ON Semiconductor®

SCHOTTKY BARRIER RECTIFIER 1.0 AMPERES, 40 VOLTS



M = Date Code BCJ = Device Code

ORDERING INFORMATION

Device	Package	Shipping [†]
MBRM140T1	POWERMITE	3000/Tape & Reel
MBRM140T1G	POWERMITE (Pb-Free)	3000/Tape & Reel
MBRM140T3	POWERMITE	12000/Tape & Reel
MBRM140T3G	POWERMITE (Pb-Free)	12000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

⁼ Pb–Free Package

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	40	V
Average Rectified Forward Current (At Rated V_R , $T_C = 110^{\circ}C$)	Ι _Ο	1.0	А
Peak Repetitive Forward Current (At Rated V _R , Square Wave, 100 kHz, T _C = 110°C)	I _{FRM}	2.0	A
Non-Repetitive Peak Surge Current (Non-Repetitive peak surge current, halfwave, single phase, 60 Hz)	I _{FSM}	50	A
Storage Temperature	T _{stg}	–55 to 150	°C
Operating Junction Temperature	TJ	-55 to 125	°C
Voltage Rate of Change (Rated V_R , $T_J = 25^{\circ}C$)	dv/dt	10,000	V/μs

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Lead (Anode) (Note 1)	R _{tjl}	35	°C/W
Thermal Resistance, Junction-to-Tab (Cathode) (Note 1)	R _{tjtab}	23	
Thermal Resistance, Junction-to-Ambient (Note 1)	R _{tja}	277	

1. Mounted with minimum recommended pad size, PC Board FR4, See Figures 9 & 10

ELECTRICAL CHARACTERISTICS

Rating Symbol Value		lue	Unit	
Maximum Instantaneous Forward Voltage (Note 2), See Figure 2	VF	T _J = 25°C	T _J = 85°C	V
$(I_F = 0.1 \text{ A})$ $(I_F = 1.0 \text{ A})$ $(I_F = 3.0 \text{ A})$		0.36 0.55 0.85	0.30 0.515 0.88	
Maximum Instantaneous Reverse Current (Note 2), See Figure 4	I _R	T _J = 25°C	T _J = 85°C	mA
(V _R = 40 V) (V _R = 20 V)		0.5 0.15	25 18	

2. Pulse Test: Pulse Width \leq 250 $\mu s,$ Duty Cycle \leq 2%



MBRM140



reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of T_J therefore must include forward and reverse power effects. The allowable operating T_J may be calculated from the equation: $T_J = T_{Jmax} - r(t)(Pf + Pr)$ where

- r(t) = thermal impedance under given conditions,
- Pf = forward power dissipation, and
- Pr = reverse power dissipation

This graph displays the derated allowable T_J due to reverse bias under DC conditions only and is calculated as $T_J = T_{Jmax} - r(t)Pr$, where r(t) = R thia. For other power applications further calculations must be performed.

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PACKAGE DIMENSIONS

POWERMITE CASE 457-04



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.75	2.05	0.069	0.081
В	1.75	2.18	0.069	0.086
C	0.85	1.15	0.033	0.045
D	0.40	0.69	0.016	0.027
F	0.70	1.00	0.028	0.039
Н	-0.05	+0.10	-0.002	+0.004
J	0.10	0.25	0.004	0.010
K	3.60	3.90	0.142	0.154
L	0.50	0.80	0.020	0.031
R	1.20	1.50	0.047	0.059
S	0.50	REF	0.019	REF

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.